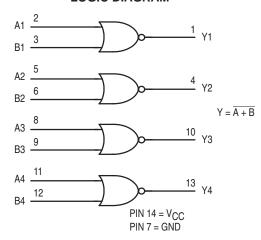
Quad 2-Input NOR Gate

High-Performance Silicon-Gate CMOS

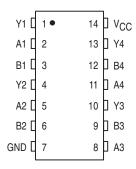
The MC74HC02A is identical in pinout to the LS02. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 40 FETs or 10 Equivalent Gates

LOGIC DIAGRAM



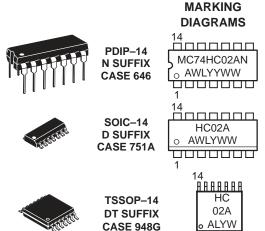
PIN ASSIGNMENT





ON Semiconductor

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A = Assembly Location

HBBBBBB

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

FUNCTION TABLE

Inp	Output	
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

ORDERING INFORMATION

Device	Package	Shipping
MC74HC02AN	PDIP-14	2000 / Box
MC74HC02AD	SOIC-14	55 / Rail
MC74HC02ADR2	SOIC-14	2500 / Reel
MC74HC02ADT	TSSOP-14	96 / Rail
MC74HC02ADTR2	TSSOP-14	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
Vcc	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Functional operation should be restricted to the Recommended Operating Conditions.

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			Vcc	V
TA	Operating Temperature, All Package Typ	oes	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	٧
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	>
		V_{in} = V_{IH} or V_{IL} $ I_{out} \le 2.4$ mA $ I_{out} \le 4.0$ mA $ I_{out} \le 5.2$ mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.7 5.2	

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{Out}} \leq 2.4 \text{ mA} \\ & I_{\text{Out}} \leq 4.0 \text{ mA} \\ & I_{\text{Out}} \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μА
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $ I_{out} = 0 \mu A$	6.0	1.0	10	40	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

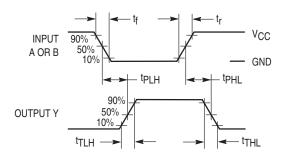
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

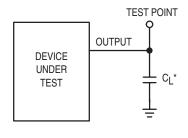
			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
tPLH, tPHL	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

			Typical @ 25°C, V _{CC} = 5.0 V	
١	C_{PD}	Power Dissipation Capacitance (Per Gate)*	22	pF

^{*} Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).



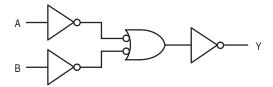


*Includes all probe and jig capacitance

Figure 1. Switching Waveforms

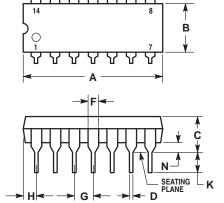
Figure 2. Test Circuit

EXPANDED LOGIC DIAGRAM (1/4 OF THE DEVICE)



PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE L



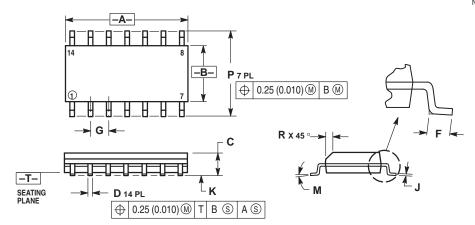


- NOTES:
 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.
 2. DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
 3. DIMENSION B DOES NOT INCLUDE MOLD

 - FLASH.
 4. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN MAX		MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145 0.185 0.015 0.021 0.040 0.070		3.69	4.69
D			0.38	0.53
F			1.02	1.78
G	0.100	BSC	2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F



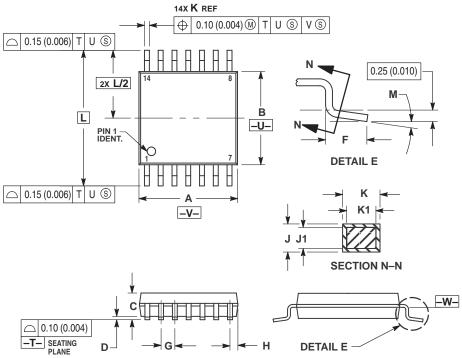
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI DIMENSIONING AND TOLERANCING PER ANS Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWARD E DAMBAR.

 - PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	0 BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE O**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BOOM ON TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С	_	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0 °	8°	0.0	8 °	

Notes

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<u>Data Sheet</u> Quad 2-Input NOR Gate 154 kB PDF

Device MC74HC02A

Quad 2-Input NOR Gate

High-Performance Silicon-Gate CMOS

The MC74HC02A is identical in pinout to the LS02. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

Features:

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard
- Chip Complexity: 40 FETs or 10 Equivalent Gates

Orderable Parts

Action	Orderable Part	Short Desc.	Package Desc.	Pin Count	Case Outline	<u>Status</u>	Price/Unit	Pack Qty
N/A	MC74HC02AFEL	Tape and Reel	SOIC EIAJ	14	940A-03	Active	\$0.160	2000
KI/A	MOZALICOGAD	Oa	000	4 /	751 / 00	۸ ماند ۸	ቀህ ተርህ	EE

IN/A	IVIU/4NUUZAU	Quau 2- Input NOR Gate	SUIU	14	/31A-U3	ACIIVE	φυ. ισυ	၁၁
N/A	MC74HC02ADR2	Tape and Reel	SOIC	14	751A-03	Active	\$0.160	2500
N/A	MC74HC02ADT	Quad 2- Input NOR Gate	TSSOP	14	948G-01	Active	\$0.200	96
N/A	MC74HC02ADTEL	Tape and Reel	TSSOP	14	948G-01	Active	\$0.200	2000
N/A	MC74HC02ADTR2	Tape and Reel	TSSOP	14	948G-01	Active	\$0.200	2500
N/A	MC74HC02AF	Quad 2- Input NOR Gate	SOIC EIAJ	14	940A-03	Active	\$0.160	50
N/A	MC74HC02AFL1	Tape and Reel	SOIC EIAJ	14	940A-03	LifeTime		
N/A	MC74HC02AFL2	Tape and Reel	SOIC EIAJ	14	940A-03	LifeTime		
N/A	MC74HC02AFR1	Tape and Reel	SOIC EIAJ	14	940A-03	LifeTime		
N/A	MC74HC02AFR2	Tape and Reel	SOIC EIAJ	14	940A-03	LifeTime		
N/A	MC74HC02AN	Quad 2- Input NOR Gate	PDIP	14	646-06	Active	\$0.160	500

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